AMENDMENTS TO THE SPECIFICATION:

Page 1, before the heading "BACKGROUND OF THE INVENTION," please replace the insert submitted in the Preliminary Amendment of August 19, 2003 (See page 2 thereof) with the amended insert as follows:

"CROSS-REFERENCE TO RELATED APPLICATIONS"

This application is a Continuation application of Application Serial No. ~~09/215,105~~09/715,105, filed November 20, 2000, now U.S. Patent No. 6,636,280, the entire disclosure of which is hereby incorporated by reference.

Page 4, please replace the paragraph beginning on line 12 with the amended paragraph as follows:

Japanese Patent Application Laid-open No. Hei 11-40501 (laid-open Feb. 12, 1999)discloses a prior art which first forms a polycrystalline silicon film by irradiating a laser beam onto the first layer made of an amorphous silicon film, then forms the second layer made of an amorphous silicon film on the first layer made of the polycrystalline silicon film, and then ~~convert~~ converts the second layer made of the amorphous silicon film into a polycrystalline silicon film by irradiating a laser beam onto the second layer of the amorphous silicon film.

Page 4, please replace the paragraph beginning on line 21, and bridging to page 5, line 7, with the amended paragraph as follows:

But, in the technique of Japanese Patent Application Laid-open No. Hei 10-41234, there was not a concept of removing impurities from the first layer made of the polycrystalline silicon ~~film, therefore~~film; therefore, regions having large concentrations of impurities are present at an interface between the first and second layers made of the polycrystalline silicon films and the impurities hinder the

polycrystalline silicon films of the first and second layers from melting ~~together, and consequentlytogether~~. Consequently, this made it difficult to obtain an integral polycrystalline silicon film having good crystal quality and free from boundaries between the first and second layers made of the polycrystalline silicon films.

Page 5, please replace the paragraph on line 14 with the amended paragraph as follows:

Japanese Patent Application Laid-open No. Hei 7-99321 (laid-open on Apr. 11, 1995)discloses a technique which first forms the first layer made of a polycrystalline silicon film, then ~~stack~~ stacks the second layer made of an amorphous silicon film on the first layer of the polycrystalline silicon film without exposing the polycrystalline film to the atmosphere, and then ~~convert~~ converts the second layer of the amorphous silicon film into a polycrystalline silicon film by irradiating a laser beam onto the amorphous silicon film.

Page 5, please replace the paragraph beginning on line 23, and bridging to page 6, line 9, with the amended paragraph as follows:

But, in the technique of Japanese Patent Application Laid-open No. Hei 7-99321, there ~~was not~~ is no teaching therein of a concept of planarizing a surface of a polycrystalline silicon film, and therefore the technique did not include a cleaning process for removing protrusions produced in the first layer of the polycrystalline silicon film by irradiation of the laser beam before stacking the second layer of the amorphous silicon film on the first layer of the polycrystalline silicon film. Consequently, in the technique of Japanese Patent Application Laid-open No. Hei 7-99321, it was difficult to obtain a polycrystalline silicon film having a very flat surface, unlike the present invention.

Page 8, please replace the paragraph beginning on line 25, and bridging to page 9, line 8, with the amended paragraph as follows:

(3) Generally source and drain regions are formed by first forming the insulating layer as explained in (1) above, next coating an electrode material on the insulating layer and patterning the electrode material film into the gate electrode and then introducing impurities into the polycrystalline silicon film by a technique such as ion implantation. In this case also, a contour of an equal-impurity concentration becomes uneven and protrudent with respect to a surface of the substrate like the case of (2) above.

Page 9, please replace the paragraph beginning on line 15, with the amended paragraph as follows:

~~It is objects~~ Included among the objectives of the present invention are to provide a liquid crystal display device having an active matrix substrate including stable low-voltage high-speed thin film transistors by solving the above-explained problems with the prior art and thereby reducing unevenness of the polycrystalline silicon semiconductor layer, ~~making~~ to make the insulating layer thinner and ~~flattening~~ flatten the lateral distributions of impurity concentrations, and to provide a method of fabricating the liquid crystal display device.